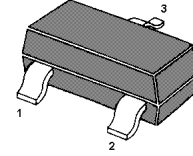




PNP Silicon Epitaxial Planar Transistor

For switching and general purpose applications.

The transistor is subdivided into three groups P, Q and R, according to its DC current gain.



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	40	V
Collector Emitter Voltage	-V _{CEO}	32	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	500	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	-55 to +150	°C

Characteristics at T_{amb}=25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at -V _{CE} =3V, -I _C =100mA Current Gain Group	P	82	-	180	-
	Q	120	-	270	-
	R	180	-	390	-
	h _{FE}				
Collector-base breakdown voltage at -I _C =100μA	-V _{(BR)CBO}	40	-	-	V
Collector-emitter breakdown voltage at -I _C =1mA	-V _{(BR)CEO}	32	-	-	V
Emitter-base breakdown voltage at -I _C =100μA	-V _{(BR)EBO}	5	-	-	V
Collector Cutoff Current at -V _{CB} =20V	-I _{CBO}	-	-	1	μA
Emitter Cutoff Current at -V _{EB} =4V	-I _{EBO}	-	-	1	μA
Collector Saturation Voltage at -I _C =300mA, -I _B =30mA	-V _{CE(sat)}	-	-	0.6	V
Transition Frequency at -V _{CE} =5V, -I _E =20mA, f=100MHz	f _T	-	200	-	MHz
Collector Output Capacitance at -V _{CB} =10V, f=1MHz	Cob	-	7	-	pF



CHINA BASE
INTERNATIONAL

SOT-23



MMBTSA1036

www.china-base.com.hk

Typical Characteristics

